

Shun-Ichiro Ohmi

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Multi-level 2-bit/cell operation utilizing Hf-based metal/oxide/nitride/oxide/silicon nonvolatile memory with HfO ₂ and HfON tunneling layer. Japanese Journal of Applied Physics, 2022, 61, SB1001.	1.5	0
2	Investigation of random telegraph noise characteristics of Hf-based MONOS nonvolatile memory devices with HfO ₂ and HfON tunneling layers. Japanese Journal of Applied Physics, 2022, 61, SC1066.	1.5	2
3	Effects of sputtering power on the formation of 5 nm thick ferroelectric nondoped HfO ₂ gate insulator for MFSFET application. Japanese Journal of Applied Physics, 2022, 61, SH1010.	1.5	1
4	Effect of Kr/O ₂ -Plasma Reactive Sputtering on Ferroelectric Nondoped HfO ₂ , Formation for MFSFET With Pt Gate Electrode. IEEE Transactions on Electron Devices, 2021, 68, 2427-2433.	3.0	11
5	MFSFET with 5 nm Thick Ferroelectric Undoped HfO ₂ Gate Insulator. , 2021, , .		4
6	The Effect of Si Surface Flattening Process on the MISFET With High-k HfNx Multilayer Gate Dielectrics. IEEE Transactions on Semiconductor Manufacturing, 2021, 34, 328-332.	1.7	0
7	Investigation of the HfON Tunneling Layer of MONOS Device for Low-Voltage and High-Speed Operation Nonvolatile Memory Application. IEEE Transactions on Semiconductor Manufacturing, 2021, 34, 323-327.	1.7	3
8	Ferroelectric Hafnium Nitride Thin Films Directly Formed on Si(100) Substrate. IEEE Journal of the Electron Devices Society, 2021, 9, 1036-1040.	2.1	1
9	Reduction of process temperature for Si surface flattening utilizing Ar/H ₂ ambient annealing and its application to SOI-MISFETs with bilayer HfN high-k gate insulator. Japanese Journal of Applied Physics, 2020, 59, SCCB02.	1.5	3
10	Bias-voltage-dependent measurement of apparent barrier height on low-work-function thin film. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2020, 38, 062801.	1.2	2
11	Low-Voltage Operation of MFSFET with Ferroelectric Nondoped HfO ₂ Formed by Kr/O ₂ -Plasma Sputtering. , 2020, , .		4
12	High-k LaBxNy gate insulator formed by the Ar/N2 plasma sputtering of N-doped LaB6 metal thin films and its application to floating-gate memory. , 2020, , .		0
13	Improvement of Hf-based metal/oxide/nitride/oxide/Si nonvolatile memory characteristics by Si surface atomically flattening. Japanese Journal of Applied Physics, 2020, 59, SGGB10.	1.5	5
14	Ferroelectric Gate Field-Effect Transistors with 10nm Thick Nondoped HfO ₂ Utilizing Pt Gate Electrodes. IEICE Transactions on Electronics, 2020, E103.C, 280-285.	0.6	7
15	In-Situ N ₂ -Plasma Nitridation for High-k HfN Gate Insulator Formed by Electron Cyclotron Resonance Plasma Sputtering. IEICE Transactions on Electronics, 2020, E103.C, 299-303.	0.6	2
16	The influence of Hf interlayers for ferroelectric non-doped HfO ₂ with suppressing the interfacial layer formation. Japanese Journal of Applied Physics, 2019, 58, SIIB16.	1.5	7
17	Work Function and Electronic Structure Measurements on Nitrogen-Doped LaB6 Thin Film by Scanning Tunneling Microscope. , 2019, , .		0
18	The Effect of PMA with TiN Gate Electrode on the Formation of Ferroelectric Undoped HfO ₂ Directly Deposited on Si(100). IEICE Transactions on Electronics, 2019, E102.C, 435-440.	0.6	8

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19	Ferroelectric HfO ₂ formation by annealing of a HfO ₂ /Hf/HfO ₂ /Si(100) stacked structure. Japanese Journal of Applied Physics, 2019, 58, SBBB08.	1.5	6
20	Ultrathin HfN Multilayer Gate Insulator Formation with High Dielectric Constant Induced by Interface Polarization. , 2019, , .		4
21	The Effect of Kr/O ₂ Sputtering on the Ferroelectric Properties of SrBi ₂ Ta ₂ O ₉ Thin Film Formation. IEICE Transactions on Electronics, 2019, E102.C, 441-446.	0.6	2
22	Improvement of Endurance Characteristics for Al-Gate Hf-Based MONOS Structures on Atomically Flat Si(100) Surface Realized by Annealing in Ar/H ₂ Ambient. IEICE Transactions on Electronics, 2018, E101.C, 328-333.	0.6	10
23	In situ formation of Hf-based metal/oxide/nitride/oxide/silicon structure for nonvolatile memory application. Japanese Journal of Applied Physics, 2018, 57, 114201.	1.5	10
24	Ferroelectric properties of undoped HfO ₂ directly deposited on Si substrates by RF magnetron sputtering. Japanese Journal of Applied Physics, 2018, 57, 11UF09.	1.5	14
25	Multi-level 2-bit/cell operation utilizing Hf-based MONOS nonvolatile memory. , 2018, , .		1
26	Influence of Si(100) surface flattening process on nonvolatile memory characteristics of Hf-based MONOS structures. , 2017, , .		3
27	Investigation of bilayer HfN _x gate insulator utilizing ECR plasma sputtering. IEICE Electronics Express, 2016, 13, 20160054-20160054.	0.8	12
28	In-situ formation of Hf-based MONOS structures for non-volatile memory applications. IEICE Electronics Express, 2015, 12, 20150969-20150969.	0.8	11
29	Variability Improvement by Si Surface Flattening of Electrical Characteristics in MOSFETs With High-k HfON Gate Insulator. IEEE Transactions on Semiconductor Manufacturing, 2015, 28, 266-271.	1.7	13
30	Si Surface Orientation Dependence on the Electrical Characteristics of HfN Gate Insulator with sub-0.5 nm EOT Formed by ECR Plasma Sputtering. Materials Research Society Symposia Proceedings, 2014, 1588, 1.	0.1	6
31	Excellent Current Drivability and Environmental Stability in Room-Temperature-Fabricated Pentacene-Based Organic Field-Effect Transistors With $\{m \text{ HfO}}_{2}\}$ Gate Insulators. IEEE Transactions on Electron Devices, 2014, 61, 569-575.	3.0	18
32	Importance of Si surface flatness to realize high-performance Si devices utilizing ultrathin films with new material system. IEICE Electronics Express, 2014, 11, 20142006-20142006.	0.8	18
33	Experimental demonstration of a ferroelectric FET using paper substrate. IEICE Electronics Express, 2014, 11, 20140447-20140447.	0.8	5
34	Potential of MISFET with HfN gate dielectric formed by ECR plasma sputtering. Electronics Letters, 2013, 49, 500-501.	1.0	12
35	Impact of Si surface roughness on MOSFET characteristics with ultrathin HfON gate insulator formed by ECR plasma sputtering. IEICE Electronics Express, 2013, 10, 20130651-20130651.	0.8	13
36	Contact resistivity reduction for PtSi/Si(100) by dopant segregation process. IEICE Electronics Express, 2013, 10, 20130778-20130778.	0.8	8

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37	Hafnium-nitride gate insulator formed by electron-cyclotron-resonance plasma sputtering. IEICE Electronics Express, 2012, 9, 1329-1334.	0.8	14
38	Fully Room-Temperature-Fabricated Low-Voltage Operating Pentacene-Based Organic Field-Effect Transistors With HfON Gate Insulator. IEEE Electron Device Letters, 2011, 32, 1600-1602.	3.9	5
39	Performance improvement of pentacene based organic field-effect transistor with HfON gate insulator. IEICE Electronics Express, 2011, 8, 1461-1466.	0.8	5
40	Selective etching of HfN gate electrode for HfN/HfSiON gate stack in-situ formations. IEICE Electronics Express, 2011, 8, 1492-1497.	0.8	4
41	Low contact resistivity of barrier height controlled PtHfSi to Si evaluated by cross-bridge Kelvin resistor. IEICE Electronics Express, 2011, 8, 1710-1715.	0.8	7
42	Work function modulation of PtSi by alloying with Yb. IEICE Electronics Express, 2011, 8, 33-37.	0.8	7
43	A study on precise control of PtSi work function by alloying with Hf. IEICE Electronics Express, 2011, 8, 45-49.	0.8	8
44	Impact of Kr gas mixing in oxygen plasma etching of ferroelectric poly(vinylidene fluoride) (P(VDF/TrFE)) thin films. Journal of Applied Physics, 2011, 110, 044101.	3.3	8
45	Investigation of PDA process to improve electrical characteristics of HfO ₂ /SiO ₂ /N ₂ O ₂ /SiO ₂ /Si system. High-k dielectric formed by ECR plasma oxidation of HfN. , 2007, , .		4
46	Effect of ultra-thin Ti layer on PtSi work function modulation. , 2005, , .		2
47	A Study on Selective Etching of SiGe Layers in SiGe/Si Systems for Device Applications. Materials Research Society Symposia Proceedings, 2003, 795, 194.	0.1	0
48	Effect of ultrathin Mo and MoSix layer on Ti silicide reaction. Journal of Applied Physics, 1999, 86, 3655-3660.	2.5	22
49	CMOS downsizing and high-K gate insulator technology. , 0, , .		1
50	Advanced gate dielectric materials for sub-100 nm CMOS. , 0, , .		48
51	Effects of gas phase absorption into Si substrates on plasma doping process. , 0, , .		1